

# Contents

<b>1</b>	<b>Surface and Interface Physics: Its Definition and Importance . . .</b>	<b>1</b>
	Panel I: Ultrahigh Vacuum (UHV) Technology . . . . .	6
	Panel II: Basics of Particle Optics and Spectroscopy . . . . .	17
	Problems . . . . .	28
<b>2</b>	<b>Preparation of Well-Defined Surfaces, Interfaces and Thin Films .</b>	<b>29</b>
	2.1 Why Is Ultrahigh Vacuum Used? . . . . .	29
	2.2 Cleavage in UHV . . . . .	31
	2.3 Ion Bombardment and Annealing . . . . .	34
	2.4 Evaporation and Molecular Beam Epitaxy (MBE) . . . . .	35
	2.5 Epitaxy by Means of Chemical Reactions . . . . .	43
	Panel III: Auger Electron Spectroscopy (AES) . . . . .	49
	Panel IV: Secondary Ion Mass Spectroscopy (SIMS) . . . . .	55
	Problems . . . . .	63
<b>3</b>	<b>Morphology and Structure of Surfaces, Interfaces and Thin Films</b>	<b>65</b>
	3.1 Surface Stress, Surface Energy, and Macroscopic Shape . . . . .	65
	3.2 Relaxation, Reconstruction, and Defects . . . . .	71
	3.3 Two-Dimensional Lattices, Superstructure, and Reciprocal Space	76
	3.3.1 Surface Lattices and Superstructures . . . . .	76
	3.3.2 2D Reciprocal Lattice . . . . .	79
	3.4 Structural Models of Solid–Solid Interfaces . . . . .	80
	3.5 Nucleation and Growth of Thin Films . . . . .	85
	3.5.1 Modes of Film Growth . . . . .	85
	3.5.2 “Capillary Model” of Nucleation . . . . .	89
	3.6 Film-Growth Studies: Experimental Methods and Some Results .	92
	Panel V: Scanning Electron Microscopy (SEM) and Microprobe Techniques . . . . .	105
	Panel VI: Scanning Tunneling Microscopy (STM) . . . . .	111
	Panel VII: Surface Extended X-Ray Absorption Fine Structure (SEXAFS) . . . . .	121
	Problems . . . . .	127

<b>4</b>	<b>Scattering from Surfaces and Thin Films</b>	129
4.1	Kinematic Theory of Surface Scattering	130
4.2	The Kinematic Theory of Low-Energy Electron Diffraction	135
4.3	What Can We Learn from Inspection of a LEED Pattern?	137
4.4	Dynamic LEED Theory, and Structure Analysis	142
4.4.1	Matching Formalism	143
4.4.2	Multiple-Scattering Formalism	146
4.4.3	Structure Analysis	146
4.5	Kinematics of an Inelastic Surface Scattering Experiment	148
4.6	Dielectric Theory of Inelastic Electron Scattering	152
4.6.1	Bulk Scattering	153
4.6.2	Surface Scattering	156
4.7	Dielectric Scattering on a Thin Surface Layer	161
4.8	Some Experimental Examples of Inelastic Scattering of Low-Energy Electrons at Surfaces	167
4.9	The Classical Limit of Particle Scattering	172
4.10	Conservation Laws for Atomic Collisions: Chemical Surface Analysis	176
4.11	Rutherford BackScattering (RBS): Channeling and Blocking	179
	Panel VIII: Low-Energy Electron Diffraction (LEED) and Reflection High-Energy Electron Diffraction (RHEED)	189
	Panel IX: X-Ray Diffraction (XRD) for Thin Film Characterisation	197
	Panel X: Electron Energy Loss Spectroscopy (EELS)	208
	Problems	216
<b>5</b>	<b>Surface Phonons</b>	217
5.1	The Existence of “Surface” Lattice Vibrations on a Linear Chain	218
5.2	Extension to a Three-Dimensional Solid with a Surface	222
5.3	Rayleigh Waves	223
5.4	The Use of Rayleigh Waves as High-Frequency Filters	228
5.5	Surface-Phonon (Plasmon) Polaritons	230
5.6	Dispersion Curves from Experiment and from Realistic Calculations	239
	Panel XI: Atom and Molecular Beam Scattering	245
	Problems	251
<b>6</b>	<b>Electronic Surface States</b>	253
6.1	Surface States for a Semi-Infinite Chain in the Nearly-Free Electron Model	254
6.2	Surface States of a 3D Crystal and Their Charging Character	258
6.2.1	Intrinsic Surface States	258
6.2.2	Extrinsic Surface States	262
6.3	Aspects of Photoemission Theory	263
6.3.1	General Description	263
6.3.2	Angle-Integrated Photoemission	267
6.3.3	Bulk- and Surface-State Emission	269

6.3.4	Symmetry of Initial States and Selection Rules . . . . .	271
6.3.5	Many-Body Aspects . . . . .	272
6.4	Some Surface-State Band Structures for Metals . . . . .	275
6.4.1	<i>s</i> - and <i>p</i> -like Surface States . . . . .	275
6.4.2	<i>d</i> -like Surface States . . . . .	278
6.4.3	Empty and Image-Potential Surface States . . . . .	284
6.5	Surface States on Semiconductors . . . . .	287
6.5.1	Elemental Semiconductors . . . . .	289
6.5.2	III–V Compound Semiconductors . . . . .	297
6.5.3	Group III Nitrides . . . . .	302
6.5.4	II–VI Compound Semiconductors . . . . .	306
6.6	Spin-Orbit Coupling in Surface States . . . . .	309
6.6.1	Spin-Orbit Coupling in a 2-dimensional Electron Gas . . . . .	309
6.6.2	Spin-Split Surface States on Au and Semimetal Surfaces . . . . .	314
6.6.3	Surface States on Topological Insulators . . . . .	316
Panel XII:	Photoemission and Inverse Photoemission . . . . .	325
Problems	. . . . .	335
<b>7</b>	<b>Space-Charge Layers at Semiconductor Interfaces</b> . . . . .	<b>337</b>
7.1	Origin and Classification of Space-Charge Layers . . . . .	337
7.2	The Schottky Depletion Space-Charge Layer . . . . .	342
7.3	Weak Space-Charge Layers . . . . .	344
7.4	Space-Charge Layers on Highly Degenerate Semiconductors . . . . .	346
7.5	The General Case of a Space-Charge Layer and Fermi-level Pinning . . . . .	348
7.6	Quantized Accumulation and Inversion Layers . . . . .	351
7.7	Some Particular Interfaces and Their Surface Potentials . . . . .	356
7.8	The Silicon MOS Field-Effect Transistor . . . . .	366
7.9	Magnetic Field Induced Quantization . . . . .	370
7.10	Two-Dimensional Plasmons . . . . .	373
Panel XIII:	Optical Surface Techniques . . . . .	376
Problems	. . . . .	391
<b>8</b>	<b>Metal–Semiconductor Junctions and Semiconductor Heterostructures</b> . . . . .	<b>393</b>
8.1	General Principles Governing the Electronic Structure of Solid–Solid Interfaces . . . . .	393
8.2	Metal-Induced Gap States (MIGS) at the Metal–Semiconductor Interface . . . . .	401
8.3	Virtual Induced Gap States (VIGS) at the Semiconductor Heterointerface . . . . .	410
8.4	Structure- and Chemistry-Dependent Models of Interface States . . . . .	415
8.5	Some Applications of Metal–Semiconductor Junctions and Semiconductor Heterostructures . . . . .	422
8.5.1	Schottky Barriers . . . . .	422
8.5.2	Semiconductor Heterojunctions and Modulation Doping . . . . .	425

8.5.3	The High Electron Mobility Transistor (HEMT) . . . . .	430
8.6	Quantum Effects in 2D Electron Gases at Semiconductor Interfaces . . . . .	432
Panel XIV: Electrical Measurements of Schottky-Barrier Heights and Band Offsets . . . . .		440
Problems . . . . .		447
<b>9</b>	<b>Collective Phenomena at Interfaces: Superconductivity and Ferromagnetism . . . . .</b>	<b>449</b>
9.1	Superconductivity at Interfaces . . . . .	450
9.1.1	Some General Remarks . . . . .	451
9.1.2	Fundamentals of Superconductivity . . . . .	453
9.1.3	Andreev Reflection . . . . .	459
9.1.4	A Simple Model for Transport Through a Normal Conductor–Superconductor Interface . . . . .	462
9.2	Josephson Junctions with Ballistic Transport . . . . .	468
9.2.1	Josephson Effects . . . . .	468
9.2.2	Josephson Currents and Andreev Levels . . . . .	470
9.2.3	Subharmonic Gap Structures . . . . .	475
9.3	An Experimental Example of a Superconductor–Semiconductor 2DEG–Superconductor Josephson Junction . . . . .	476
9.3.1	Preparation of the Nb–2DEG–Nb Junction . . . . .	477
9.3.2	Critical Currents Through the Nb–2DEG–Nb Junction . . . . .	478
9.3.3	The Current Carrying Regime . . . . .	480
9.3.4	Supercurrent Control by Non-equilibrium Carriers . . . . .	481
9.4	Ferromagnetism at Surfaces and within Thin Films . . . . .	484
9.4.1	The Band Model of Ferromagnetism . . . . .	484
9.4.2	Ferromagnetism in Reduced Dimensions . . . . .	487
9.5	Magnetic Quantum Well States . . . . .	493
9.6	Magnetic Interlayer Coupling . . . . .	497
9.7	Giant Magnetoresistance and Spin-Transfer Torque Mechanism . . . . .	499
9.7.1	Giant Magnetoresistance (GMR) . . . . .	499
9.7.2	Magnetic Anisotropies and Magnetic Domains . . . . .	503
9.7.3	Spin-Transfer Torque Effect: A Magnetic Switching Device . . . . .	508
Panel XV: Magneto-Optical Characterization: Kerr Effect . . . . .		514
Panel XVI: Spin-Polarized Scanning Tunneling Microscopy (SP-STM) . . . . .		519
Problems . . . . .		525
<b>10</b>	<b>Adsorption on Solid Surfaces . . . . .</b>	<b>527</b>
10.1	Physisorption . . . . .	527
10.2	Chemisorption . . . . .	530
10.3	Work-Function Changes Induced by Adsorbates . . . . .	537
10.4	Two-Dimensional Phase Transitions in Adsorbate Layers . . . . .	542
10.5	Adsorption Kinetics . . . . .	549
Panel XVII: Desorption Techniques . . . . .		556
Panel XVIII: Kelvin-Probe and Photoemission Measurements for the Study of Work-Function Changes and Semiconductor Interfaces . . . . .		564
Problems . . . . .		571

<b>References</b>	573
Chapter 1	573
Chapter 2	573
Chapter 3	574
Chapter 4	576
Chapter 5	577
Chapter 6	577
Chapter 7	580
Chapter 8	581
Chapter 9	582
Chapter 10	583
<b>Index</b>	585

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